

Contents

1	Introduction	page 1
2	The binary collision	7
2.1	Fundamentals	7
2.1.1	Scattering by a central force field	7
2.1.2	Inelastic scattering	10
2.1.3	The two-body scattering problem	12
2.1.4	Velocity components and energy transfer	16
2.1.5	Determination of the scattering angle and the time integrals	18
2.1.6	Cross-sections	23
2.1.7	Potentials used in binary collision calculations	26
2.2	Applications	31
2.2.1	Rutherford scattering	31
2.2.2	Surface spectroscopy using shadow cones	34
2.2.3	Projectile stopping	36
2.3	Conclusion	38
3	Interatomic potentials	39
3.1	General principles	39
3.1.1	<i>Ab initio</i> potentials	41
3.2	The repulsive wall potential	44
3.2.1	The screened Coulomb potential for the isolated atom	44
3.2.2	Two-body screened Coulomb potentials	46
3.3	The attractive well potential	49
3.3.1	The Lennard-Jones potential	50
3.3.2	The Morse potential	52
3.3.3	Ionic potentials	55
3.3.4	Lattice sums for ionic potentials	58
3.3.5	Many-body empirical potentials	61
3.3.6	Fitting procedures	61

3.3.7	The Finnis–Sinclair method and the embedded atom method for metals	62
3.3.8	Covalent materials	66
3.4	The overlap potential	67
3.5	Conclusion	69
4	Electronic energy loss models	72
4.1	Introduction	72
4.2	Electronic stopping for low energies	74
4.2.1	Firsov’s semi-classical model (local)	74
4.2.2	Lindhard and Scharff electronic stopping (non-local)	79
4.2.3	Oen and Robinson electronic stopping	80
4.3	Z_1 oscillations in the electronic stopping	81
4.4	Z_2 oscillations in the electronic stopping	84
4.5	Electronic stopping for high-energy ions	86
4.6	Ion–electron interaction with regard to MD simulations	91
4.7	Summary	97
5	Transport models	99
5.1	The Boltzmann transport equation	99
5.1.1	Introduction	99
5.1.2	The forward transport equation	100
5.1.3	The backward transport equation	102
5.1.4	The time-independent Boltzmann equation	103
5.1.5	Remarks	104
5.2	Ion penetration	105
5.2.1	The energy loss distribution	105
5.2.2	Range distribution: small deflections	109
5.2.3	Range distribution: the general case	116
5.2.4	High energy	123
5.2.5	Numerical solution	123
5.3	Effects upon the target	127
5.3.1	Introduction	127
5.3.2	The transport equation: the recoil term	128
5.3.3	Deposited energy distribution: equal mass cases	130
5.3.4	Deposited energy distribution: non-equal mass cases	132
5.3.5	The distribution of displaced atoms	133
5.4	Sputtering	140
5.5	Mixing	146
5.5.1	Introduction	146
5.5.2	Modelling ion-beam atomic mixing	147
5.5.3	The diffusion approximation	153

5.5.4	A mixing example	154
5.6	Conclusion	158
6	The rest distribution of primary ions in amorphous targets	161
6.1	Introduction	161
6.2	Ion-solid interaction	162
6.3	A random solid	165
6.4	MC simulation	168
6.4.1	Non-uniform random variables	168
6.4.2	Algorithms	169
6.5	Transport equations	171
6.5.1	Derivation of a Lindhard-type TE	171
6.5.2	Moments solution of a plane source TE	173
6.5.3	TEs using the <i>gas</i> and <i>liquid</i> target models	176
6.5.4	Numerical solution of Lindhard-type TEs	178
6.5.5	Coupling relations	179
6.5.6	Implementation	179
6.6	Spatial moments of implantation profiles	180
6.6.1	Projections	180
6.6.2	Moments about the origin	181
6.6.3	Vertical moments about $\langle z \rangle$	181
6.6.4	Lateral moments	182
6.6.5	Mixed moments	183
6.7	Generating profiles in one and two dimensions	183
6.7.1	The Pearson family of frequency curves	185
6.8	Models for depth-dependent lateral moments	191
6.9	Comparison of TE and MC computer codes	194
6.9.1	Moments	194
6.9.2	1-D profiles	194
6.9.3	2-D profiles	199
6.10	Additional remarks	200
7	Binary collision algorithms	203
7.1	Introduction	203
7.2	Collisions	204
7.3	Event store models	205
7.4	The genealogy of a binary collision program	206
7.4.1	Next event algorithms	206
7.4.2	Event ordering	209
7.4.3	Non-linear events	210
7.4.4	Multiple collisions	212
7.4.5	Incident ion distributions	212

7.4.6	Full cascade models	214
7.4.7	Random materials – Monte Carlo models	215
7.4.8	Input parameters	216
7.4.9	Single-crystal materials – deterministic models	218
7.5	Dynamic models	219
7.5.1	Dose effects	219
7.5.2	Annealing effects	222
7.6	Applications	224
7.6.1	Ion scattering spectroscopy	224
7.6.2	Sputtering	228
7.6.3	Trajectories and displaced particles	231
7.7	Conclusions	231
8	Molecular dynamics	234
8.1	Equations of motion	234
8.2	Numerical integration algorithms	235
8.2.1	Hamiltonian systems	235
8.2.2	Constraint dynamics	239
8.2.3	Numerical integration algorithms for non-Hamiltonian systems	241
8.3	Neighbour lists for short-ranged potentials	242
8.4	Construction of the neighbour lists	244
8.5	The cell index method	245
8.6	Timestep control	246
8.7	The moving atom approximation	248
8.8	Boundary conditions	249
8.8.1	Constant temperature–constant pressure molecular dynamics	251
8.9	Electronic energy losses in MD	252
8.10	Lattice generation	253
8.11	Lattice vibrations	254
8.12	Ensembles of trajectories	256
8.13	Applications of molecular dynamics to surface phenomena	258
8.13.1	Angular distributions of ejected particles	259
8.13.2	The depth of origin of ejected particles	262
8.13.3	Ejected atom energy distributions	262
8.13.4	Atoms per single ion (ASI) distributions	264
8.13.5	Yield variation with incidence angle: impact collision SIMS	267
8.13.6	Cluster ejection	268
8.13.7	Cluster beams	270
8.13.8	Radiation damage in metals	272
8.13.9	Radiation damage in semiconductors	274

8.13.10	Ion implantation	275
8.13.11	Ion scattering and surface skipping motion	276
8.13.12	Crystal growth	278
8.14	Conclusion	282
9	Surface topography	284
9.1	Introduction	284
9.2	Cellular models of deposition and erosion	285
9.3	Continuum models of deposition and erosion	291
9.3.1	Isotropic erosion and deposition	291
9.3.2	Non-isotropic erosion	293
9.4	Re-deposition	302
9.5	Other secondary effects	305
9.6	Conclusion	305
	<i>Index</i>	307